JCT825F 25A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withst

Peak gate current (t_p=20μs , T_j=125)	I_{GM}	5	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

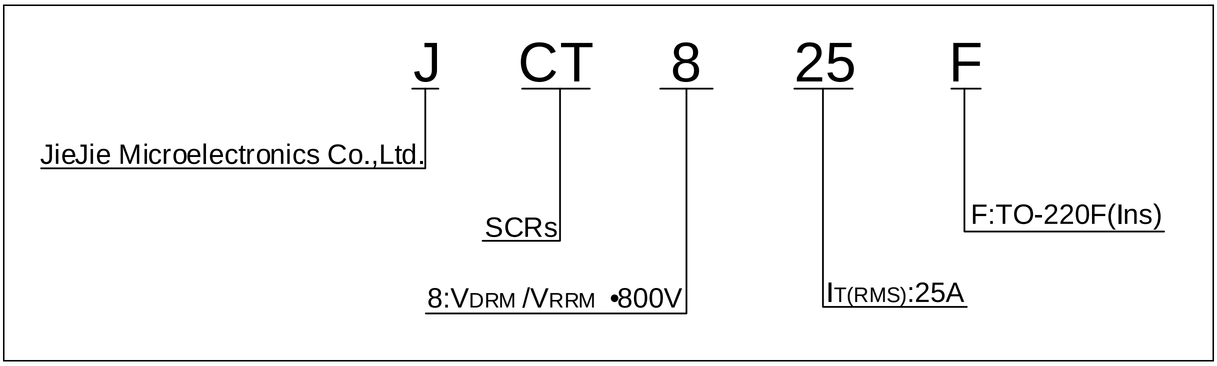
ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	**Test Condition**	**Value**			**Unit**
		MIN.	**TYP.**	**MAX.**	
I_{GT}	V_D=12V R_L=33Ω	-	-	20	mA
V_{GT}		-	-	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3kΩ	0.2	-	-	V
I_L	I_G=1.2I_{GT}	-	-	70	mA
I_H	I_T=500mA	-	-	60	mA
dV/dt	V_D=540V Gate Open T_j=125	1000	-	-	V/μs
t_{on}	I_G=20mA I_A=200mA I_R=20mA T_j=25	-	2	-	μs
t_{off}		-	50	-	

STATIC CHARACTERISTICS

Symbol	**Parameter**		**Value(MAX.)**	**Unit**
V_{TM}	I_{TM}=50A t_p=380μs	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.72	V
R_D	Dynamic resistance	T_j=125	16	mΩ

ORDERING INFORMATION



MARKING

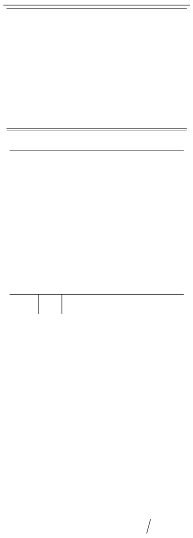


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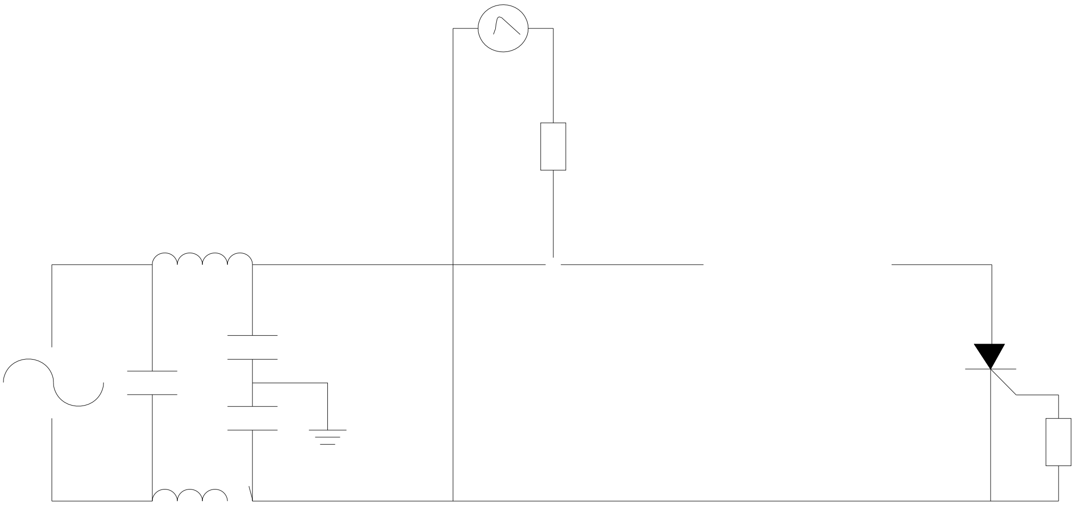
FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT825F	**800**	**20**	**TO-220F(Ins)**	**50**	**Tube**

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Sept.29, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA